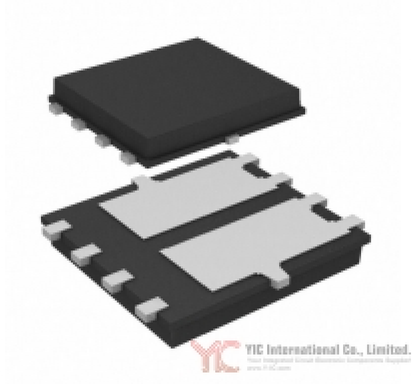


Image may be representation.
See specs for product details.

SI7909DN-T1-E3

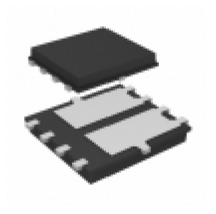
Hersteller-Teilenummer:	SI7909DN-T1-E3
Hersteller / Marke:	Electro-Films (EFI) / Vishay
Teil der Beschreibung:	MOSFET 2P-CH 12V 5.3A 1212-8
Datenblätter:	SI7909DN-T1-E3.pdf
RoHs Status:	Bleifrei / RoHS-konform
Lagerzustand:	New original, 3086 pcs Stock Available.
Liefern von:	Hong Kong
Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

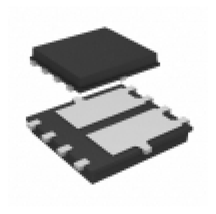
Teilenummer	SI7909DN-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2P-CH 12V 5.3A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	3086 pcs Stock
detaillierte Beschreibung	Mosfet Array 2 P-Channel (Dual) 12V 5.3A 1.3W
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.3W
Verpackung / Gehäuse	PowerPAK® 1212-8 Dual
Supplier Device-Gehäuse	PowerPAK® 1212-8 Dual
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.3A
Rds On (Max) @ Id, Vgs	37 mOhm @ 7.7A, 4.5V
VGS (th) (Max) @ Id	1V @ 700µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI7909DN-T1-E3 ist neu im Original, Suche SI7909DN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7909DN-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7909DN-T1-E3: Info@Y-IC.com

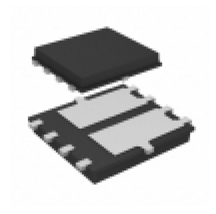
Sie können auch interessiert sein:



SI7911DN-T1-E3
Vishay / Siliconix
MOSFET 2P-CH 20V 4.2A 1212-8

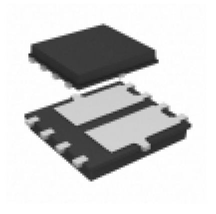


SI7909DN-T1-GE3
Electro-Films (EFI) / Vishay
MOSFET 2P-CH 12V 5.3A 1212-8

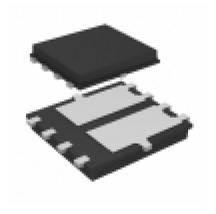


SI7905DN-T1-E3
Electro-Films (EFI) / Vishay
MOSFET 2P-CH 40V 6A 1212-8

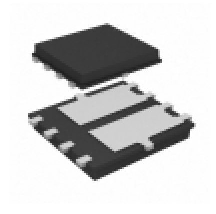
SI7904DN..
V
V QFN8



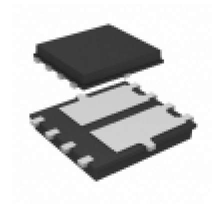
SI7909DN-T1-E3
Vishay / Siliconix
MOSFET 2P-CH 12V 5.3A 1212-8



SI7909DN-T1-GE3
Vishay / Siliconix
MOSFET 2P-CH 12V 5.3A 1212-8



SI7905DN-T1-E3
Vishay / Siliconix
MOSFET 2P-CH 40V 6A 1212-8



SI7905DN-T1-GE3
Vishay / Siliconix
MOSFET 2P-CH 40V 6A PPAK 1212-8

heiße Teile

Mehr

- SI7900AEDN-T1
- SI7900AEDN-T1-E3
- SI7900AEDN-T1-E3
- SI7900AEDN-T1-GE3
- SI7900AEDN-T1-GE3
- SI7900EDN
- SI7900EDN-T1
- SI7900EDN-T1-E3
- SI7900EDN-T1-GE3
- SI7901EDN-T1
- SI7901EDN-T1-E3
- SI7901EDN-T1-E3
- SI7904BDN-T1-E3
- SI7904BDN-T1-E3
- SI7904BDN-T1-GE3
- SI7904BDN-T1-GE3
- SI7904DN
- SI7904DN-T1
- SI7904DN-T1-E3
- SI7904DN-T1-E3
- SI7904DN-T1-GE3
- SI7904DN-T1-GE3
- SI7905DN-T1-GE3
- SI7905DN-T1-GE3
- SI7909DN-T1-E3
- SI7909DN-T1-GE3
- SI7909DN-T1-GE3
- SI7911DN
- SI7911DN-T1-E3
- SI7911DN-T1-E3
- SI7911DN-T1-GE3
- SI7911DN-T1-GE3
- SI7913DN-T1-E3
- SI7913DN-T1-E3
- SI7913DN-T1-GE3
- SI7913DN-T1-GE3
- SI7922DN-T1-E3
- SI7922DN-T1-E3
- SI7922DN-T1-GE3
- SI7922DN-T1-GE3
- SI7923DN-T1-E3
- SI7923DN-T1-E3
- SI7923DN-T1-GE3
- SI7923DN-T1-GE3
- SI7938DP-T1-GE3
- SI7938DP-T1-GE3
- SI7940DP
- SI7940DP-T1-E3
- SI7940DP-T1-E3
- SI7941DP-T1-E3

Contact us:**Info@Y-IC.com**
HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.